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Kind regards,

Team Nexperia

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

Rev. 4 — 19 December 2011

Product data sheet

1. Product profile

1.1 General description

NPN/NPN double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

	Table 1.	Product	overview
--	----------	---------	----------

Type number	e number Package		NPN/PNP	PNP/PNP	Package
	NXP	JEITA	complement	complement	configuration
PEMH18	SOT666	-	PEMD18	PEMB18	ultra small and flat lead
PUMH18	SOT363	SC-88	PUMD18	PUMB18	very small

1.2 Features and benefits

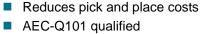
- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
lo	output current		-	-	100	mA
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		1.7	2.1	2.6	



Reduces component count



1

| | 2 3 *sym063*

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1	001aab555	

3. Ordering information

Table 4. Ord	Table 4. Ordering information				
Type number	Package				
	Name	Description	Version		
PEMH18	-	plastic surface-mounted package; 6 leads	SOT666		
PUMH18	SC-88	plastic surface-mounted package; 6 leads	SOT363		

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
PEMH18	6C
PUMH18	H5*

[1] * = placeholder for manufacturing site code

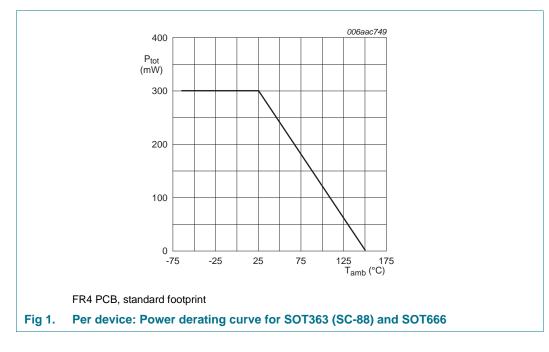
5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	-	7	V
VI	input voltage				
	positive		-	+20	V
	negative		-	-7	V
lo	output current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	PEMH18 (SOT666)		[1][2] _	200	mW
	PUMH18 (SOT363)		<u>[1]</u> -	200	mW
Per device	•				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	PEMH18 (SOT666)		[1][2] _	300	mW
	PUMH18 (SOT363)		<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω



6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PEMH18 (SOT666)		[1][2]	-	625	K/W
	PUMH18 (SOT363)		<u>[1]</u> _	-	625	K/W
Per devic	9					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PEMH18 (SOT666)		[1][2] _	-	417	K/W
	PUMH18 (SOT363)		[1] _	-	417	K/W

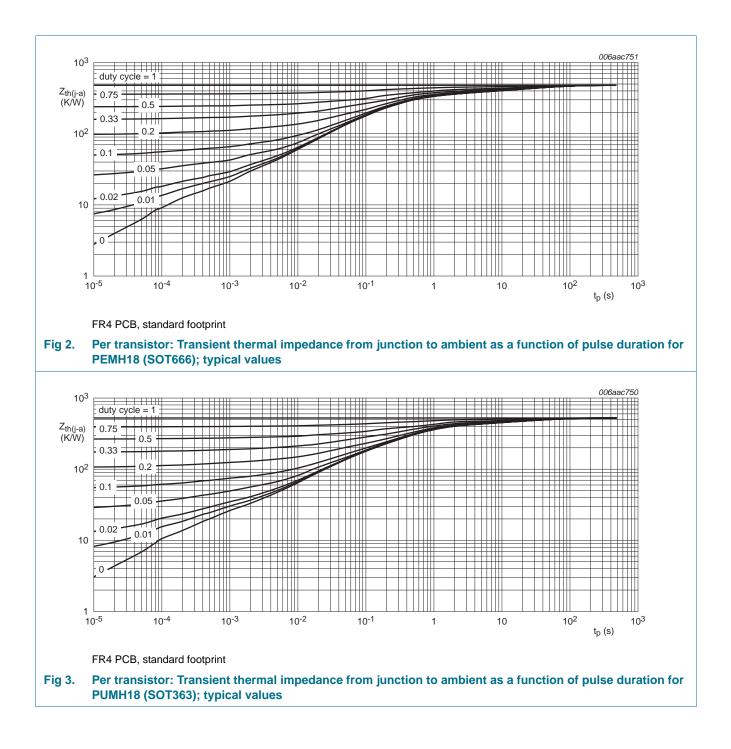
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PEMH18_PUMH18 Product data sheet

PEMH18; PUMH18

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω



7. Characteristics

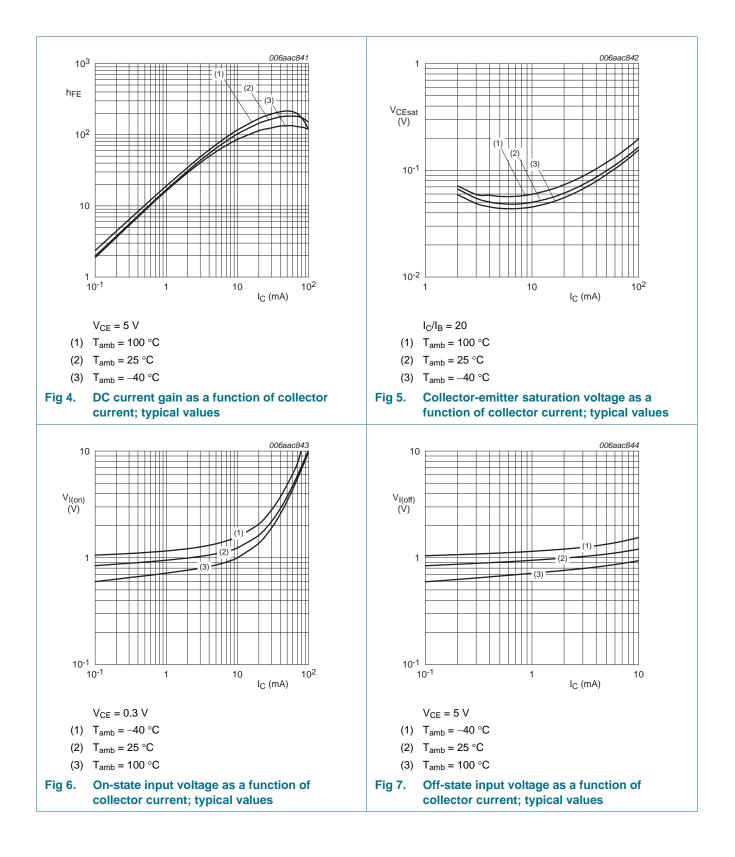
Table 8. $T_{amb} = 25$	Characteristics 5 ℃ unless otherwise spe	ecified.				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO} collector-emitter cut-off	V_{CE} = 30 V; I_B = 0 A	-	-	1	μA	
current		$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	600	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$	50	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = 10 mA; I_{B} = 0.5 mA	-	-	100	mV
V _{I(off)}	off-state input voltage	V_{CE} = 5 V; I _C = 100 μ A	-	0.9	0.3	V
V _{I(on)}	on-state input voltage	V_{CE} = 0.3 V; I_{C} = 20 mA	2.5	1.5	-	V
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		1.7	2.1	2.6	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF
f _T	transition frequency	V _{CE} = 5 V; I _C = 10 mA; f = 100 MHz	<u>[1]</u> _	230	-	MHz

[1] Characteristics of built-in transistor

PEMH18_PUMH18 Product data sheet

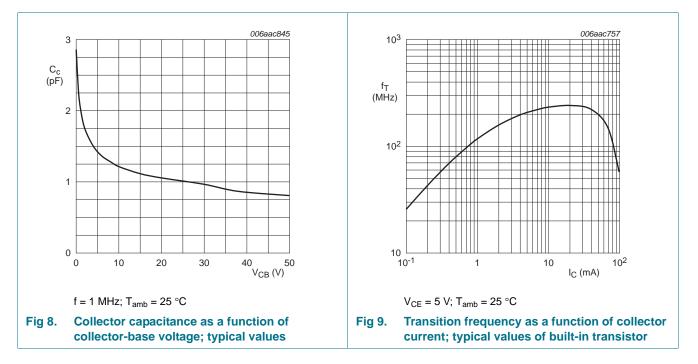
PEMH18; PUMH18

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω



PEMH18; PUMH18

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

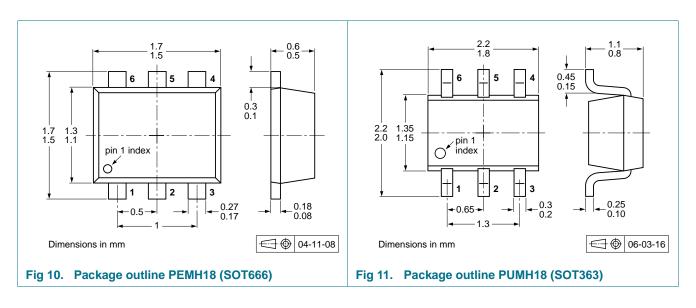


8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



PEMH18_PUMH18

10. Packing information

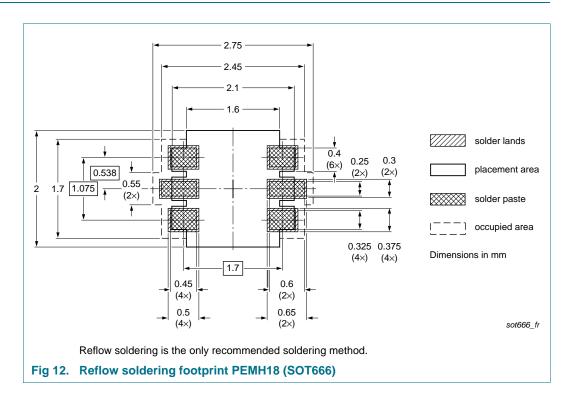
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

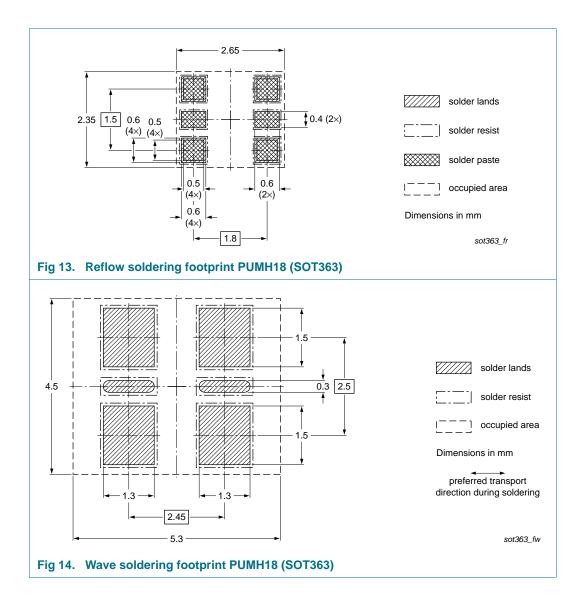
••		Description		Packing quantity			
number				3000	4000	8000	10000
PEMH18	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
PUMH18	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

- [1] For further information and the availability of packing methods, see <u>Section 14</u>.
- [2] T1: normal taping
- [3] T2: reverse taping

11. Soldering



NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω



12. Revision history

Table 10.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMH18_PUMH18 v.4	20111219	Product data sheet	-	PEMH18_PUMH18 v.3
Modifications:	 Section 4 "M Figure 1 to 3 Section 6 "TI Figure 4 to 7 Table 8 "Cha Section 8 "Te Section 11 "S 	roduct profile": updated larking": updated b, <u>8</u> and <u>9</u> : added hermal characteristics": up (: updated <u>aracteristics</u> ": I _{CEO} updated <u>est information</u> ": added <u>Soldering</u> ": added Legal information": updated	, f _T added	
PEMH18_PUMH18 v.3	20050211	Product data sheet	-	PEMH18_PUMH18 v.2
PEMH18_PUMH18 v.2	20040414	Product data sheet	-	PUMH18 v.1
PUMH18 v.1	20031016	Product specification	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PEMH18_PUMH18
Product data sheet

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

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PEMH18; PUMH18

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

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